

— Exhibition

A technical exhibition will be held during the conference. Companies that provide materials, devices, equipment and services for testing, characterization, production and development of SiC and wide-bandgap materials are encouraged to exhibit at the conference. For further details, please visit our web site (<https://icscrm2026.org/exhibition>) or contact the exhibition section of the executive committee:
e-mail: exhibition@icscrm2026.org

— Further Information

For the latest information, please visit our web site (<https://icscrm2026.org>) or contact general affairs of the executive committee:
e-mail: secretariat@icscrm2026.org

— Committees

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First Announcement and Call for Papers



International Conference on Silicon Carbide and Related Materials 2026

September 27(Sun.) - October 2 (Fri.), 2026
Yokohama, Japan

Venue: PACIFICO YOKOHAMA North, JAPAN
<https://icscrm2026.org>

Abstract Deadline: May 11, 2026



<https://icscrm2026.org>

— Scope

The aim of this conference is to discuss recent advances in crystal growth, characterization, control of material properties, device fabrication and packaging technologies, as well as system applications concerning silicon carbide (SiC) and related materials.

The objective is to enhance the materials, improve the performance and reliability of the devices, and increase productivity to expand practical applications. Ongoing work to develop implementation and circuit technologies to fully utilize the device performance will also be discussed. In the basic research field, new developments are underway, such as applications in harsh environments and quantum sensing, and these are likely to be hot topics at the conference.

The conference also serves as an international forum for the exchange of ideas on recent scientific and technical issues among researchers and engineers in industrial, academic and public sectors.

— Topics

Topics will include:

- Material and Growth

Bulk and epitaxial growth, Wafer manufacturing

- Defects and Characterization

Fundamental properties, Point and extended defects, Characterization and imaging techniques, Surface characterization and modification

- Device Process and Characterization

MOS interfaces and insulators, Device fabrication processes (e.g. Implantation, Oxidation, Surface treatments, Metallization, Ohmic and Schottky contact formations, and Dry etching technologies)

- Device Physics, Design, and Characterization

Device design and testing, Novel device concepts and Characterization, Modelling and Simulation, Novel measurements techniques

- Devices and Module Reliability, Packaging, and Applications

Modular and driver-circuit technologies, System applications, Packaging and device reliabilities

- Quantum Applications and Sensors

Theoretical and experimental studies, Optical and electrical quantum techniques, for Magnetic, Electric field, and Temperature sensors, Single-photon sources and detectors

— Important Dates

May 11, 2026	Deadline for regular abstract submission
May 31, 2026	Deadline for exhibition application
May 31, 2026	Deadline for first stage sponsorship application
July 6, 2026	Acceptance notification of regular paper
July 17, 2026	Deadline for early bird registration
August 16, 2026	Deadline for final stage sponsorship application
August 17, 2026	Deadline for late news abstract submission
August 31, 2026	Acceptance notification of late news paper
September 7, 2026	Deadline for standard registration

— Notes to Authors

The official language of the conference is English, which will be used for all presentations and printed materials. Authors are expected to present their papers in person at the conference. If authors cannot attend or wish to withdraw their paper, the technical program chair must be notified well in advance.

— Publication of Papers

The authors of accepted papers will be asked to submit manuscripts to the conference proceedings before the conference. The manuscript format and detailed instructions will be forwarded to the authors at the time of notification of acceptance.



— Location

Yokohama Minato Mirai 21 is a modern waterfront district located in the heart of Yokohama. Its name means "Port of the Future," and it is famous for its beautiful skyline by the bay. The area combines shopping, entertainment, business, and culture all in one place, including Landmark Tower, Cosmo World, Red Brick Warehouse, Yamashita Park & the Harbor Area.

Venue **PACIFICO YOKOHAMA North**

PACIFICO Yokohama North, which is located in the waterfront area of the Minato Mirai 21 district, is one of the largest convention complexes in the world. This is the newest facility of PACIFICO Yokohama, opened in 2020, that features the largest multi-purpose hall in Japan.

<https://www.pacifico.co.jp/english>



— Official Web Site

For further details on Yokohama and ICSCRM 2026, you are encouraged to visit the conference web site at:

<https://icscrm2026.org>